

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

Claim 19 (previously presented): A nitride semiconductor laser device, comprising:
a nitride semiconductor substrate;
a lower layer of nitride semiconductor grown overlying said nitride semiconductor substrate;
a light emitting layer of nitride semiconductor grown overlying said lower layer; and
an upper layer of nitride semiconductor grown overlying said light emitting layer,
wherein said upper layer has a stripe of 1.9 μm to 3.0 μm in width, a distance between an upper surface of said light emitting layer and a bottom of said stripe is 0 μm to 0.2 μm , said light emitting layer includes a structure formed of a well layer and a barrier layer stacked alternately, and said nitride semiconductor laser device includes a Fabry-Perot resonator of 300 to 1000 μm in length.

Claim 20 (previously presented): The nitride semiconductor laser device of claim 19, wherein said stripe is a ridge-geometric stripe.

Claim 21 (currently amended): The nitride semiconductor laser device of claim 19, wherein said nitride semiconductor substrate has a main surface with a plane orientation corresponding to any plane selected from the group consisting of, $[[\{001\}]]$ $\{0001\}$, $\{11-20\}$, $\{1-102\}$ and $\{1-100\}$.

Claim 22 (previously presented): The nitride semiconductor laser device of claim 21, wherein said nitride semiconductor substrate has an angle offset from said plane orientation by no more than two degrees.

Claim 23 (previously presented): The nitride semiconductor laser device of claim 19, wherein said Fabry-Perot resonator has a mirror end surface provided by $\{1-100\}$ plane.

Claim 24 (previously presented): The nitride semiconductor laser device of claim 19, wherein said well layer is two to six well layers

Claim 25 (previously presented): The nitride semiconductor laser device of claim 19, wherein said stripe is 1.9 to 2.5 μm in width.

Claim 26 (previously presented): The nitride semiconductor laser device of claim 19, wherein said light emitting layer has one of P and As added thereto.

Claim 27 (previously presented): The nitride semiconductor laser device of claim 19, wherein said lower layer includes a crack prevention layer containing In.

Claim 28 (previously presented): The nitride semiconductor laser device of claim 19, wherein said light emitting layer contains an impurity selected from the group consisting of Si, O, C, Ge, Zn, and Mg.

Claim 29 (previously presented): The nitride semiconductor laser device of claim 19, wherein said upper layer includes a carrier block layer containing Al.